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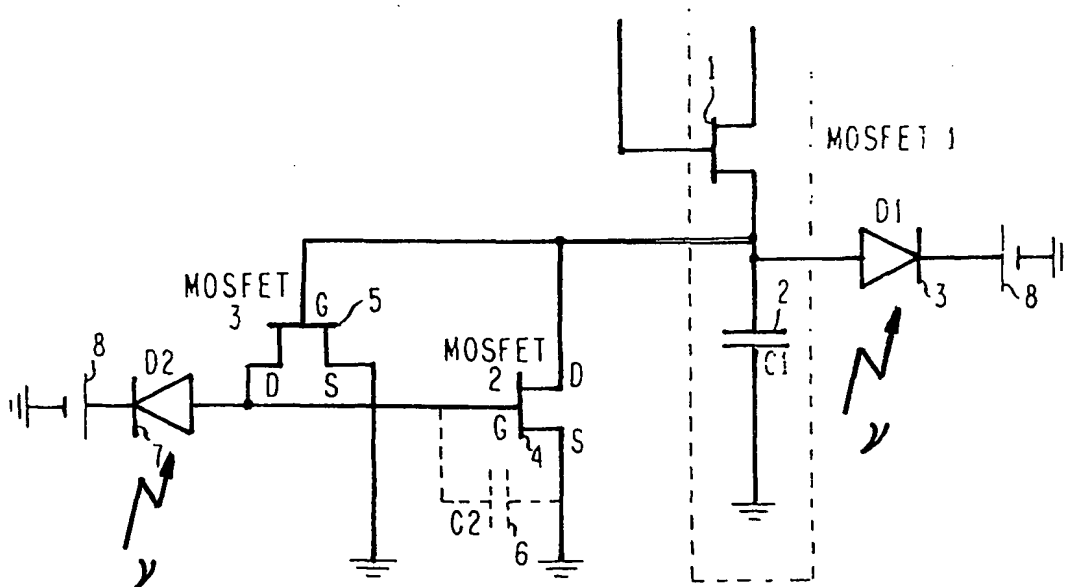
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(54) Title: SINGLE ENDED THREE TRANSISTOR QUASI-STATIC RAM CELL



(57) Abstract: A single ended three transistor quasi-static RAM cell comprises two cross coupled MOS transistors and one select MOS transistor connected to drain of one of the aforementioned MOS transistors wherein drains of both cross coupled MOS transistors are each connected to anode of one of two PN diodes functioning as constant current loads when exposed to continuous light from LED diode.

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